

FEATURES

- High reliability liquid-phase epitaxially grown GaAlAs
- 880nm peak emission for optimum matching with ODD-45W photodiode
- Wide range of linear power output
- Hermetically sealed TO-46 package
- Medium emission angle for best coverage/power density

All surfaces are gold plated. Dimensions are nominal values in inches unless otherwise specified. Window caps are welded to the case.

ELECTRO-OPTICAL CHARACTERISTICS AT 25°C

PARAMETERS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Total Power Output, P _o	I _F = 100mA	18	20		mW
Radiant Intensity, I _e			50		mW/sr
Peak Emission Wavelength, λ _p	I _F = 50mA		880		nm
Spectral Bandwidth at 50%, Δλ			80		nm
Half Intensity Beam Angle, θ				35	
Forward Voltage, V _F	I _F = 100mA		1.55	1.9	Volts
Reverse Breakdown Voltage, V _R	I _R = 10μA	5	30		Volts
Capacitance, C	V _R = 0V		17		pF
Rise Time			0.5		μsec
Fall Time			0.5		μsec

ABSOLUTE MAXIMUM RATINGS AT 25°C CASE

Power Dissipation ¹	190mW
Continuous Forward Current	100mA
Peak Forward Current (10μs, 400Hz) ²	3A
Reverse Voltage	5V
Lead Soldering Temperature (1/16" from case for 10sec)	260°C

¹Derate per Thermal Derating Curve above 25°C

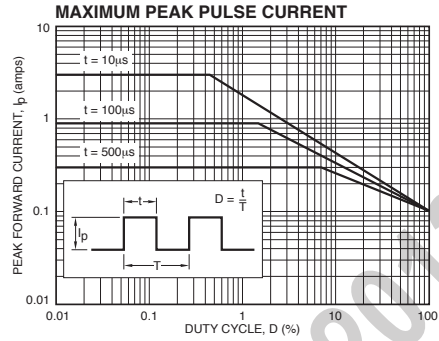
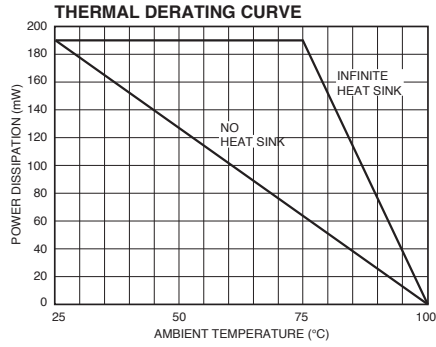
²Derate linearly above 25°C

THERMAL PARAMETERS

Storage and Operating Temperature Range	-55°C TO 100°C
Maximum Junction Temperature	100°C
Thermal Resistance, R _{THJA} ¹	400°C/W Typical
Thermal Resistance, R _{THJA} ²	135°C/W Typical



MAXIMUM RATINGS



TYPICAL CHARACTERISTICS

